DB LECTRO INC
COMPOSANTS ÉLECTRONIQUES
ELECTRONIC COMPONENTS

7830-0000-CD 780nm 3 mW Laser Diodes

Specifications

Device Laser Diode

Package Type TO-18(φ5.6mm)

●Absolute maximum ratings (Tc = 25°C)

Parameter		Symbol	Limits	Unit
Output		Po	5	mW
Reverse voltage	Laser	V_R	2	V
	PIN photodiode	$V_{R\ (PIN)}$	30	V
Operating temperature		Topr	−10～+60	℃
Storage temperature		Tstg	−40～+85	℃

●Electrical and optical characteristics (Tc = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Threshold current	I_{th}	—	35	60	mA	—
Operating current	I_{op}	—	45	70	mA	Po=3mW
Operating voltage	V_{op}	—	1.9	2.3	V	Po=3mW
Differential efficiency	η	0.1	0.25	0.6	mW/mA	$\frac{2mW}{I(3mW)-I(1mW)}$
Monitor current	I_m	0.1	0.2	0.6	mA	Po=3mW, $V_{R(PIN)}$=15V
Parallel divergence angle	$\theta_{//}$ *	8	11	15	deg	Po=3mW
Perpendicular divergence angle	$\theta_{\perp}$*	20	37	45	deg	
Parallel deviation angle	$\Delta\theta_{//}$	—	—	±2	deg	
Perpendicular deviation angle	$\Delta\theta_{\perp}$	—	—	±3	deg	
Emission point accuracy	ΔX ΔY ΔZ	—	—	±80	μm	—
Peak emission wavelength	λ	770	785	810	nm	Po=3mW
Signal-to-noise ratio	S / N	60	—	—	dB	f=720kHz, Δf=10kHz

* $\theta_{//}$ and $\theta_{\perp}$ are defined as the angle within which the intensity is 50% of the peak value.